2SC1626

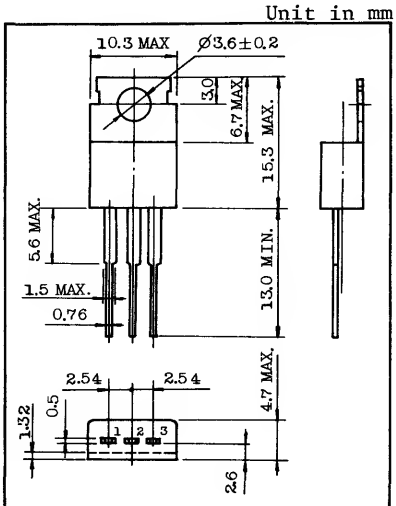
SILICON NPN EPITAXIAL TYPE (PCT PROCESS)

MEDIUM POWER AMPLIFIER APPLICATIONS.
DRIVER STAGE AMPLIFIER APPLICATIONS.

FEATURES:

- High Breakdown Voltage : V_{CEO}=80V
- Complementary to 2SA816.

Unit in mm



1. BASE
2. COLLECTOR (HEAT SINK)
3. EMITTER

JEDEC	TO-220AB
EIAJ	SC-46
TOSHIBA	2-10A1A

Mounting Kit NO. AC75
Weight : 1.9g

MAXIMUM RATINGS (Ta=25°C)

CHARACTERISTIC	SYMBOL	RAINGS	UNIT
Collector-Base Voltage	V_{CBO}	80	V
Collector-Emitter Voltage	V_{CEO}	80	V
Emitter-Base Voltage	V_{EBO}	5	V
Collector Current	I_C	750	mA
Emitter Current	I_E	-750	mA
Collector Power Dissipation	P_C	1.5	W
Junction Temperature	T_j	150	°C
Storage Temperature Range	T_{stg}	-55∿150	°C

ELECTRICAL CHARACTERISTICS (Ta=25°C)

CHARACTERISTIC		SYMBOL	TEST CONDITION	MIN.	TYP.	MAX.	UNIT
Collector Cut-off Current		I_{CBO}	V_{CB}=30V, I_E=0	-	-	0.5	μA
Emitter Cut-off Current		I_{EBO}	V_{EB}=5V, I_C=0	-	-	1.0	μA
Breakdown Voltage	Collector-Emitter	$V_{(BR)CEO}$	I_C=10mA, I_B=0	80	-	-	V
	Emitter-Base	$V_{(BR)EBO}$	I_E=0.1mA, I_C=0	5	-	-	
DC Current Gain		$h_{FE(1)}$ (Note)	V_{CE}=2V, I_C=150mA	70	-	240	
		$h_{FE(2)}$	V_{CE}=2V, I_C=500mA	40	-	-	
Collector-Emitter Saturation Voltage		$V_{CE(sat)}$	I_C=500mA, I_B=50mA	-	-	0.5	V
Base-Emitter Voltage		V_{BE}	V_{CE}=2V, I_C=500mA	-	-	1.0	V
Transition Frequency		f_T	V_{CE}=2V, I_C=150mA	50	100	-	MHz
Collector Output Capacitance		C_{ob}	V_{CB}=10V, I_E=0, f=1MHz	-	15	-	pF

Note : $h_{FE(1)}$ Classification O : 70∿140, Y : 120∿240